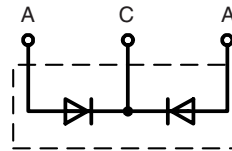


HiPerFRED™ Epitaxial Diode

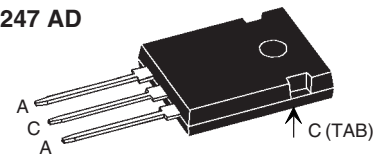
with common cathode and soft recovery

$I_{FAV} = 2 \times 30 \text{ A}$
 $V_{RRM} = 200 \text{ V}$
 $t_{rr} = 25 \text{ ns}$

V_{RSM}	V_{RRM}	Type
V	V	
200	200	DSEC 60-02A



TO-247 AD



A = Anode, C = Cathode, TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		70	A
I_{FAVM}	$T_C = 145^\circ\text{C}$; rectangular, $d = 0.5$	30	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	325	A
E_{AS}	$T_{VJ} = 25^\circ\text{C}$; non-repetitive $I_{AS} = 3 \text{ A}$; $L = 180 \mu\text{H}$	1.2	mJ
I_{AR}	$V_A = 1.5 \cdot V_R$ typ.; $f = 10 \text{ kHz}$; repetitive	0.3	A
T_{VJ}		-55...+175	$^\circ\text{C}$
T_{VJM}		175	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	165	W
M_d	mounting torque	0.8...1.2	Nm
F_c	mounting force with clip	20...120	N
Weight	typical	6	g

Features

- International standard package
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low I_{RM} -values
- Soft recovery behaviour
- Epoxy meets UL 94V-0

Applications

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{RM} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

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Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R ①	$V_R = V_{RRM}$; $T_{VJ} = 25^\circ\text{C}$		10 μA
	$V_R = V_{RRM}$; $T_{VJ} = 150^\circ\text{C}$		200 μA
V_F ②	$I_F = 30 \text{ A}$; $T_{VJ} = 150^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$		0.95 V
			1.20 V
R_{thJC}			0.9 K/W
R_{thCH}		0.25	K/W
t_{rr}	$I_F = 1 \text{ A}$; $-di/dt = 200 \text{ A}/\mu\text{s}$; $V_R = 30 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$	25	ns
I_{RM}	$V_R = 100 \text{ V}$; $I_F = 50 \text{ A}$; $-di_F/dt = 100 \text{ A}/\mu\text{s}$; $T_{VJ} = 100^\circ\text{C}$		4 A

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %

② Pulse Width = 300 μs , Duty Cycle < 2.0 %

Data according to IEC 60747 and per diode unless otherwise specified.

IXYS reserves the right to change limits, test conditions and dimensions.

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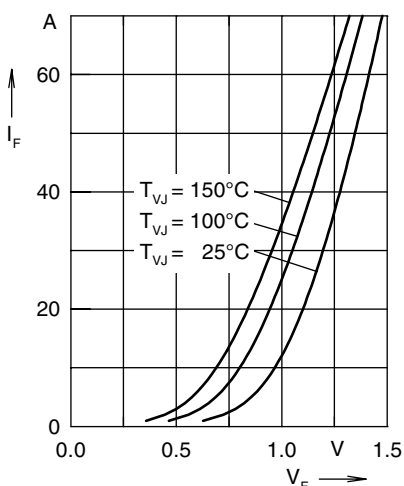


Fig.1 Forward current I_F vs. forward voltage drop V_F

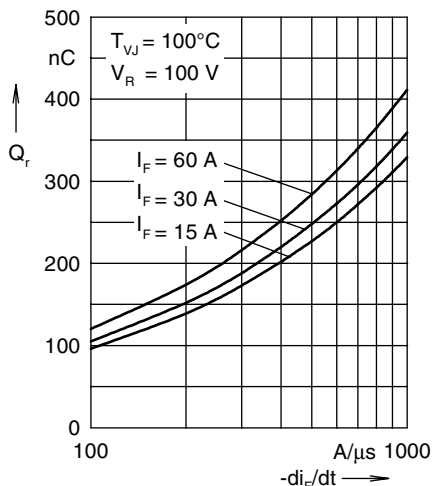


Fig.2 Reverse recovery charge Q_{rr} versus $-di_F/dt$

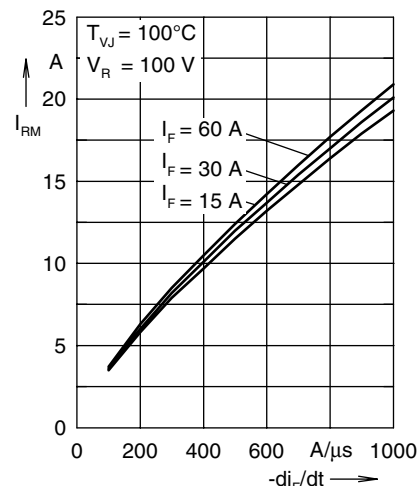


Fig.3 Peak reverse current I_{RM} versus $-di_F/dt$

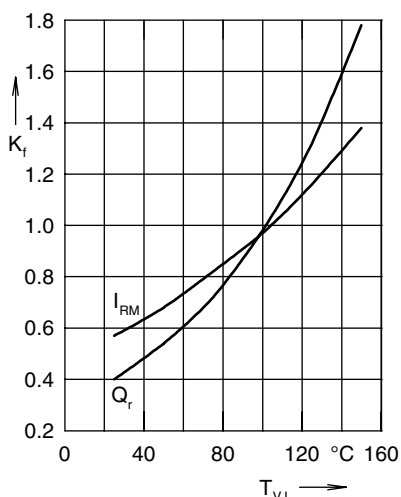


Fig.4 Dynamic parameters K_f , I_{RM} , Q_{rr} versus T_{VJ}

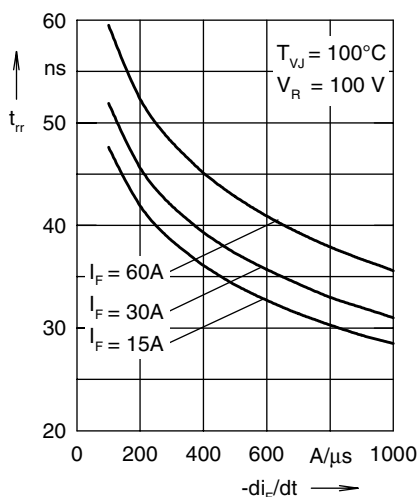


Fig.5 Reverse recovery time t_{rr} versus $-di_F/dt$

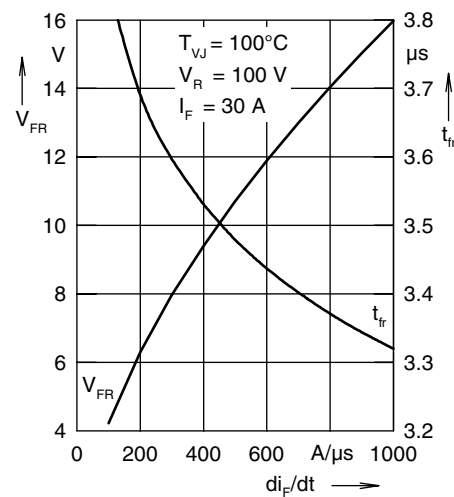


Fig.6 Peak forward voltage V_{FR} & forw. recov. time t_{fr} vs. $-di_F/dt$

NOTE: Fig. 2 to Fig. 6 shows typical values

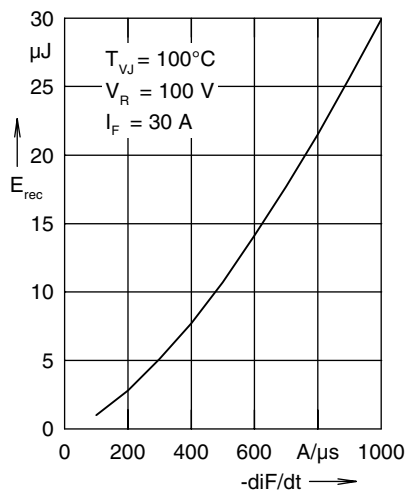


Fig.7 Recovery energy E_{rec} versus $-di_F/dt$

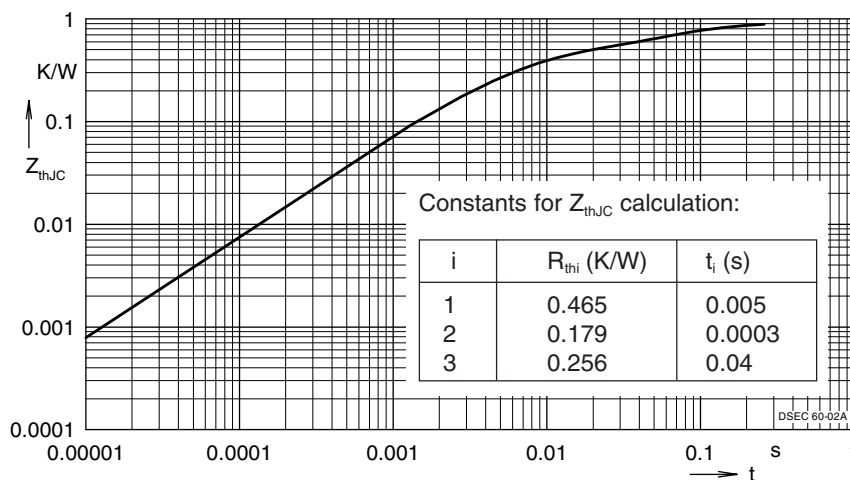


Fig.8 Transient thermal resistance junction to case